

NCE Automotive N-Channel Super Trench II Power MOSFET

Description

The NCEAP25N10AD uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

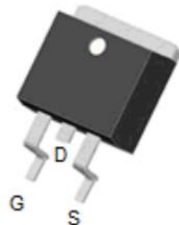
Application

- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

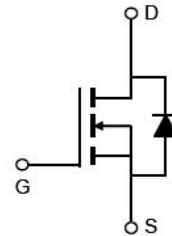
General Features

- $V_{DS} = 100V, I_D = 37A$
 $R_{DS(ON)} = 21m\Omega$ (typical) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 26m\Omega$ (typical) @ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100% ΔV_{ds} tested
- **AEC-Q101 qualified**

TO-263-2L



Top View



Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|--------------|----------------|-----------|------------|----------|
| AP25N10AD | NCEAP25N10AD | TO-263-2L | - | - | - |

Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|--------------------------|------------|---------------------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 37 | A |
| Drain Current-Continuous($T_c = 100^\circ\text{C}$) | $I_D(100^\circ\text{C})$ | 25 | A |
| Pulsed Drain Current | I_{DM} | 140 | A |
| Maximum Power Dissipation | P_D | 70 | W |
| Derating factor | | 0.47 | W/ $^\circ\text{C}$ |
| Single pulse avalanche energy ^(Note 1) | E_{AS} | 97 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | $^\circ\text{C}$ |

Thermal Characteristic

| | | | |
|--------------------------------------|-----------------|------|--------------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 2.14 | $^\circ\text{C/W}$ |
|--------------------------------------|-----------------|------|--------------------|

Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---------------------|---|-----|--------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 100 | - | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =100V, V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 1.1 | 1.7 | 2.5 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =20A | - | 21 | 25 | mΩ |
| | | V _{GS} =4.5V, I _D =20A | - | 26 | 30 | mΩ |
| Forward Transconductance | g _{FS} | V _{DS} =5V, I _D =20A | - | 19 | - | S |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =50V, V _{GS} =0V, F=1.0MHz | - | 1317.6 | - | pF |
| Output Capacitance | C _{oss} | | - | 123.9 | - | pF |
| Reverse Transfer Capacitance | C _{rss} | | - | 19.3 | - | pF |
| Switching Characteristics <small>(Note 2)</small> | | | | | | |
| Turn-on Delay Time | t _{d(on)} | V _{DD} =50V, I _D =20A V _{GS} =10V, R _G =3Ω | - | 13 | - | nS |
| Turn-on Rise Time | t _r | | - | 15 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | | - | 22 | - | nS |
| Turn-Off Fall Time | t _f | | - | 6 | - | nS |
| Total Gate Charge | Q _g | V _{DS} =50V, I _D =20A, V _{GS} =10V | - | 27.6 | - | nC |
| Gate-Source Charge | Q _{gs} | | - | 5.5 | | nC |
| Gate-Drain Charge | Q _{gd} | | - | 6.9 | | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage | V _{SD} | V _{GS} =0V, I _S =20A | - | - | 1.2 | V |
| Diode Forward Current | I _S | | - | - | 37 | A |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F = 20A | - | 40 | - | nS |
| Reverse Recovery Charge | Q _{rr} | di/dt = 100A/μs | - | 85 | - | nC |

Notes:

1. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25\Omega$
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=175^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

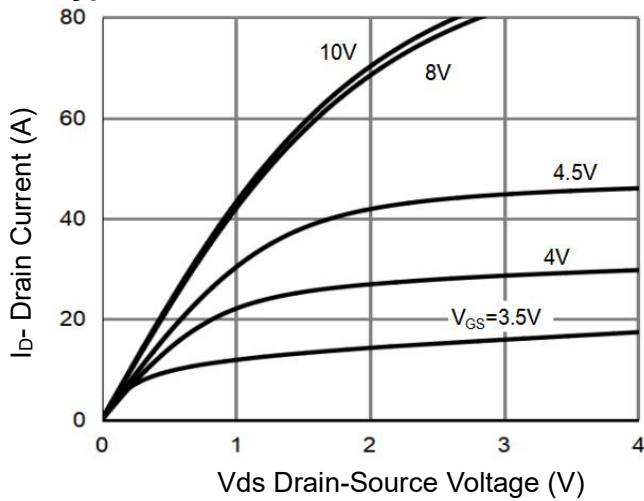


Figure 1 Output Characteristics

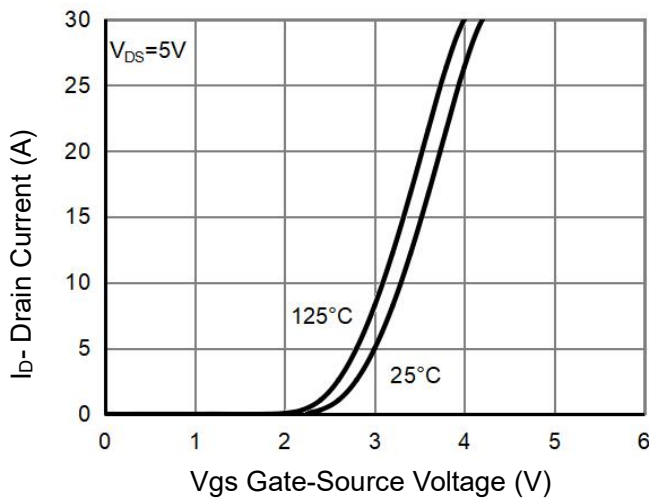


Figure 2 Transfer Characteristics

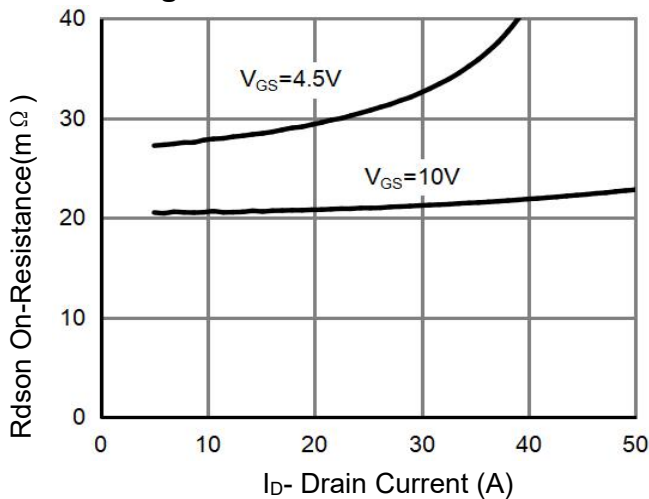


Figure 3 $R_{DS(on)}$ - Drain Current

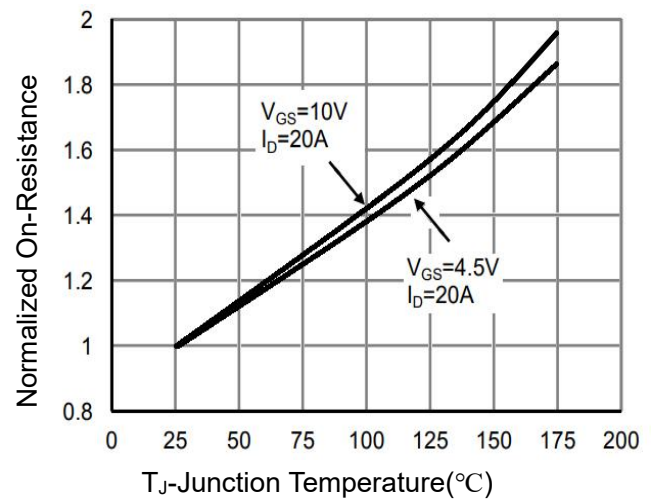


Figure 4 $R_{DS(on)}$ -Junction Temperature

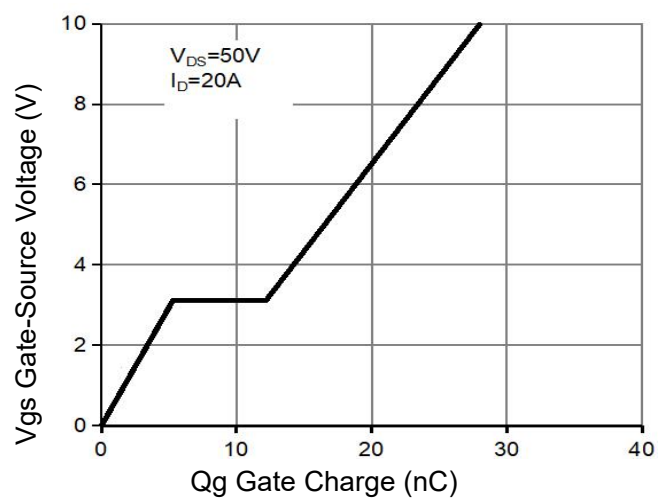


Figure 5 Gate Charge

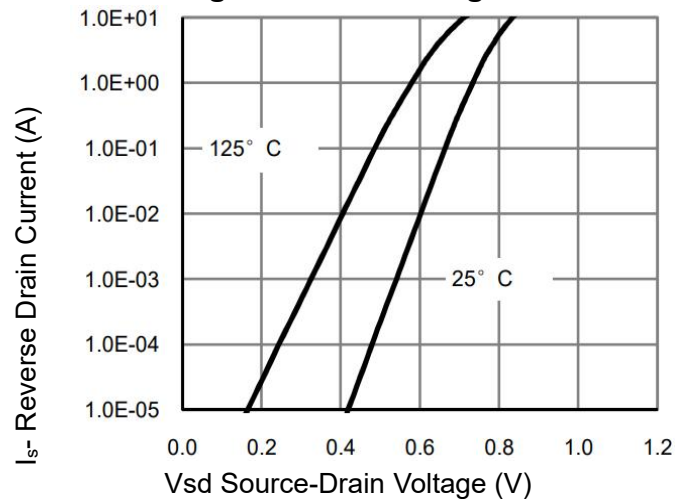


Figure 6 Source- Drain Diode Forward

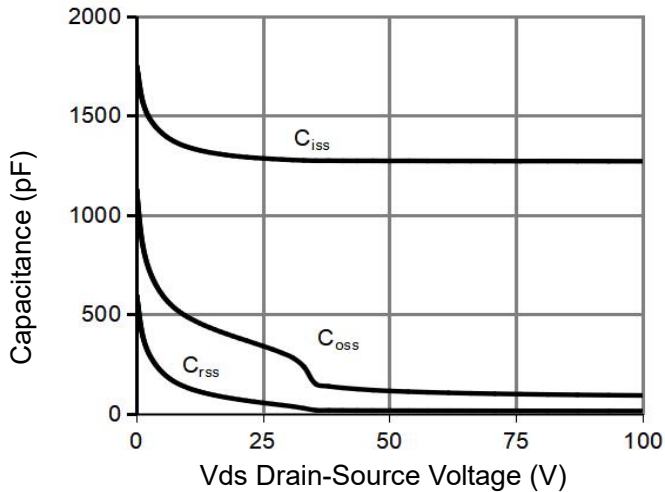


Figure 7 Capacitance vs Vds

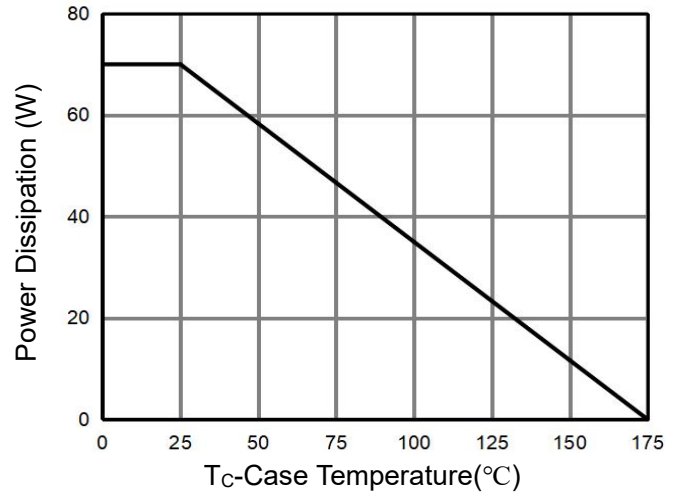


Figure 9 Power De-rating

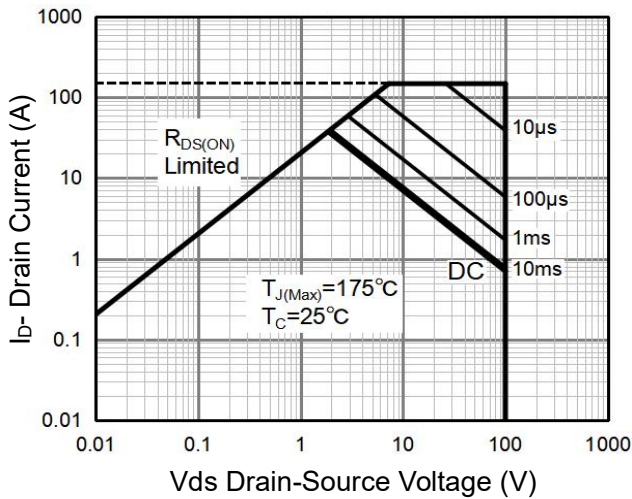


Figure 8 Safe Operation Area (Note3)

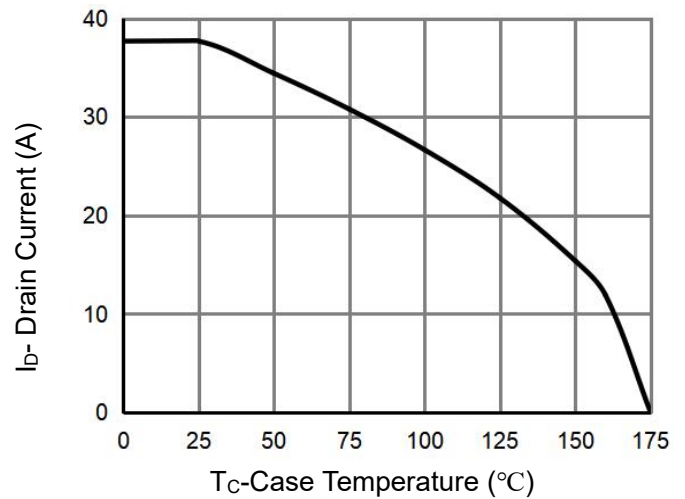


Figure 10 Current De-rating

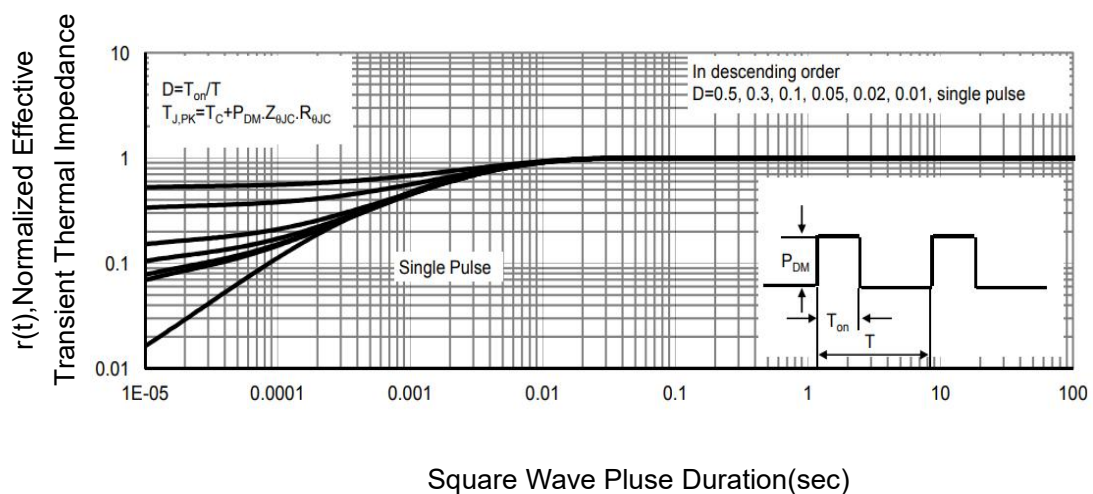
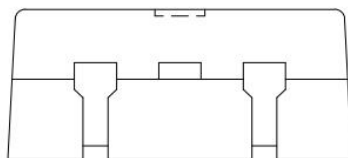
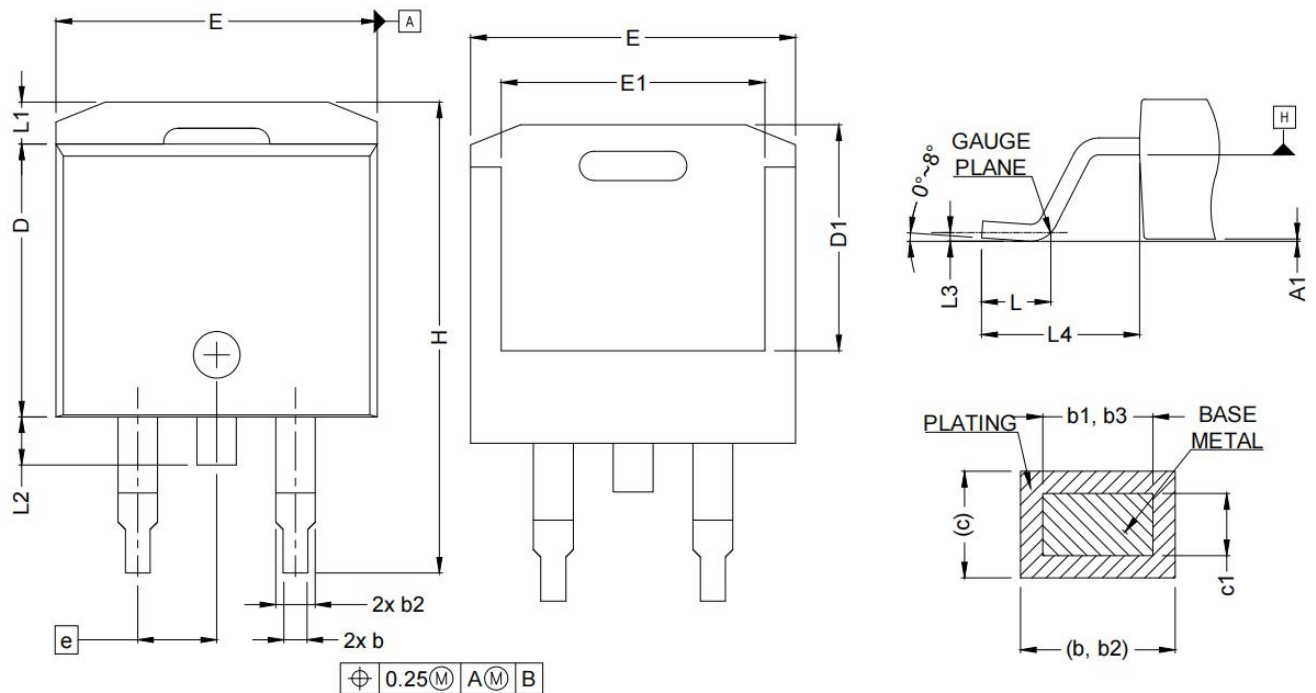


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L Package Information



OPTION 1

2 LEADs

| SYMBOL | MIN. | MAX. | SYMBOL | MIN. | MAX. |
|--------|------|------|--------|----------|-------|
| A | 4.36 | 4.56 | E | 10.15 | 10.55 |
| A1 | 0 | 0.25 | E1 | 8.10 | 8.70 |
| b | 0.70 | 0.90 | e | 2.54 BSC | |
| b1 | 0.51 | 0.89 | H | 15.00 | 15.60 |
| b2 | 1.17 | 1.37 | L | 1.90 | 2.50 |
| b3 | 1.17 | 1.37 | L1 | - | 1.65 |
| c | 0.38 | 0.69 | L2 | - | 1.78 |
| c1 | 0.38 | 0.53 | L3 | 0.25 TYP | |
| c2 | 1.19 | 1.34 | L4 | 4.78 | 5.28 |
| D | 8.60 | 9.00 | J1 | 2.56 | 2.96 |
| D1 | 6.90 | 7.50 | | | |

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